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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	291
Number of Logic Elements/Cells	2910
Total RAM Bits	59904
Number of I/O	65
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1c3t100i7

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Section I–2 Altera Corporation



2. Cyclone Architecture

C51002-1.6

Functional Description

Cyclone® devices contain a two-dimensional row- and column-based architecture to implement custom logic. Column and row interconnects of varying speeds provide signal interconnects between LABs and embedded memory blocks.

The logic array consists of LABs, with 10 LEs in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device. Cyclone devices range between 2,910 to 20,060 LEs.

M4K RAM blocks are true dual-port memory blocks with 4K bits of memory plus parity (4,608 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 36-bits wide at up to 250 MHz. These blocks are grouped into columns across the device in between certain LABs. Cyclone devices offer between 60 to 288 Kbits of embedded RAM.

Each Cyclone device I/O pin is fed by an I/O element (IOE) located at the ends of LAB rows and columns around the periphery of the device. I/O pins support various single-ended and differential I/O standards, such as the 66- and 33-MHz, 64- and 32-bit PCI standard and the LVDS I/O standard at up to 640 Mbps. Each IOE contains a bidirectional I/O buffer and three registers for registering input, output, and output-enable signals. Dual-purpose DQS, DQ, and DM pins along with delay chains (used to phase-align DDR signals) provide interface support with external memory devices such as DDR SDRAM, and FCRAM devices at up to 133 MHz (266 Mbps).

Cyclone devices provide a global clock network and up to two PLLs. The global clock network consists of eight global clock lines that drive throughout the entire device. The global clock network can provide clocks for all resources within the device, such as IOEs, LEs, and memory blocks. The global clock lines can also be used for control signals. Cyclone PLLs provide general-purpose clocking with clock multiplication and phase shifting as well as external outputs for high-speed differential I/O support.

Figure 2–1 shows a diagram of the Cyclone EP1C12 device.

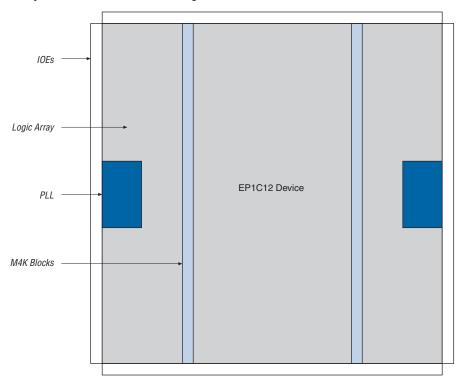


Figure 2-1. Cyclone EP1C12 Device Block Diagram

The number of M4K RAM blocks, PLLs, rows, and columns vary per device. Table 2–1 lists the resources available in each Cyclone device.

Table 2–1. Cyclone Device Resources					
Device	M4K	DI I -	LAD Columna	LAD Dawe	
Device	Columns	Blocks	PLLs	LAB Columns	LAB Rows
EP1C3	1	13	1	24	13
EP1C4	1	17	2	26	17
EP1C6	1	20	2	32	20
EP1C12	2	52	2	48	26
EP1C20	2	64	2	64	32

signal. The output registers can be bypassed. Pseudo-asynchronous reading is possible in the simple dual-port mode of M4K blocks by clocking the read enable and read address registers on the negative clock edge and bypassing the output registers.

When configured as RAM or ROM, you can use an initialization file to pre-load the memory contents.

Two single-port memory blocks can be implemented in a single M4K block as long as each of the two independent block sizes is equal to or less than half of the M4K block size.

The Quartus II software automatically implements larger memory by combining multiple M4K memory blocks. For example, two 256×16-bit RAM blocks can be combined to form a 256×32-bit RAM block. Memory performance does not degrade for memory blocks using the maximum number of words allowed. Logical memory blocks using less than the maximum number of words use physical blocks in parallel, eliminating any external control logic that would increase delays. To create a larger high-speed memory block, the Quartus II software automatically combines memory blocks with LE control logic.

Parity Bit Support

The M4K blocks support a parity bit for each byte. The parity bit, along with internal LE logic, can implement parity checking for error detection to ensure data integrity. You can also use parity-size data words to store user-specified control bits. Byte enables are also available for data input masking during write operations.

Shift Register Support

You can configure M4K memory blocks to implement shift registers for DSP applications such as pseudo-random number generators, multi-channel filtering, auto-correlation, and cross-correlation functions. These and other DSP applications require local data storage, traditionally implemented with standard flip-flops, which can quickly consume many logic cells and routing resources for large shift registers. A more efficient alternative is to use embedded memory as a shift register block, which saves logic cell and routing resources and provides a more efficient implementation with the dedicated circuitry.

The size of a $w \times m \times n$ shift register is determined by the input data width (w), the length of the taps (m), and the number of taps (n). The size of a $w \times m \times n$ shift register must be less than or equal to the maximum number of memory bits in the M4K block (4,608 bits). The total number of shift

register outputs (number of taps $n \times$ width w) must be less than the maximum data width of the M4K RAM block (×36). To create larger shift registers, multiple memory blocks are cascaded together.

Data is written into each address location at the falling edge of the clock and read from the address at the rising edge of the clock. The shift register mode logic automatically controls the positive and negative edge clocking to shift the data in one clock cycle. Figure 2–14 shows the M4K memory block in the shift register mode.

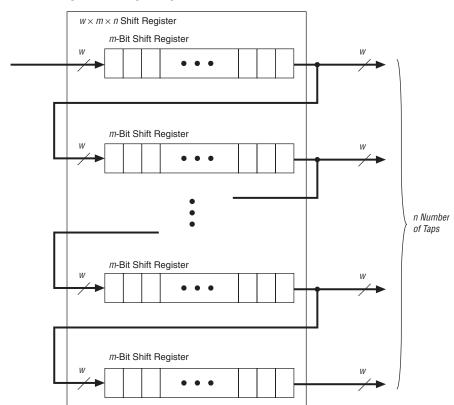


Figure 2-14. Shift Register Memory Configuration

Memory Configuration Sizes

The memory address depths and output widths can be configured as $4,096 \times 1, 2,048 \times 2, 1,024 \times 4,512 \times 8$ (or 512×9 bits), 256×16 (or 256×18 bits), and 128×32 (or 128×36 bits). The 128×32 - or 36-bit configuration

Read/Write Clock Mode

The M4K memory blocks implement read/write clock mode for simple dual-port memory. You can use up to two clocks in this mode. The write clock controls the block's data inputs, wraddress, and wren. The read clock controls the data output, rdaddress, and rden. The memory blocks support independent clock enables for each clock and asynchronous clear signals for the read- and write-side registers. Figure 2–20 shows a memory block in read/write clock mode.

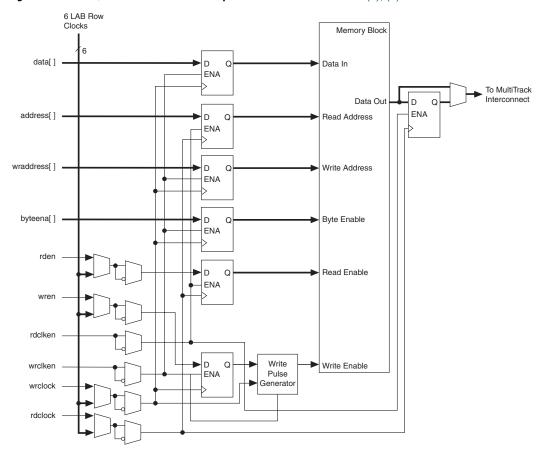


Figure 2–20. Read/Write Clock Mode in Simple Dual-Port Mode Notes (1), (2)

Notes to Figure 2–20:

- (1) All registers shown except the rden register have asynchronous clear ports.
- (2) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

The eight global clock lines in the global clock network drive throughout the entire device. The global clock network can provide clocks for all resources within the device—IOEs, LEs, and memory blocks. The global clock lines can also be used for control signals, such as clock enables and synchronous or asynchronous clears fed from the external pin, or DQS signals for DDR SDRAM or FCRAM interfaces. Internal logic can also drive the global clock network for internally generated global clocks and asynchronous clears, clock enables, or other control signals with large fanout. Figure 2–22 shows the various sources that drive the global clock network.

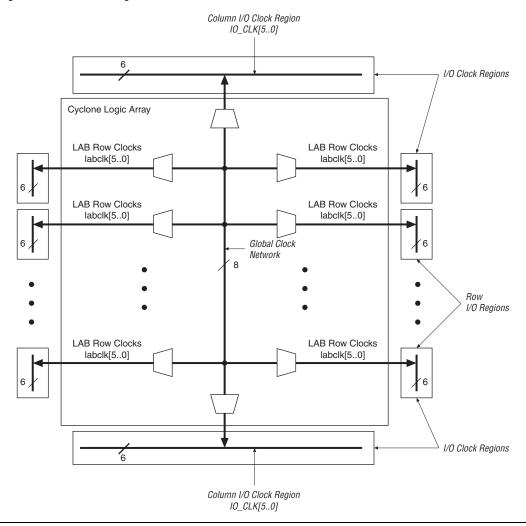
DPCLK2 DPCLK3 Cyclone Device Global Clock Network 8 DPCLK1 _ □ DPCLK4 From logic From logic array array CLK0 [□ CLK2 PLL2 PLL1 CLK1 (3) □ CLK3 (3) (2) 2 DPCLK0 [□ DPCLK5 DPCLK7 DPCLK6

Figure 2–22. Global Clock Generation Note (1)

Notes to Figure 2–22:

- (1) The EP1C3 device in the 100-pin TQFP package has five DPCLK pins (DPCLK2, DPCLK3, DPCLK4, DPCLK6, and DPCLK7).
- (2) EP1C3 devices only contain one PLL (PLL 1).
- (3) The EP1C3 device in the 100-pin TQFP package does not have dedicated clock pins CLK1 and CLK3.

Figure 2-24. I/O Clock Regions



PLLs

Cyclone PLLs provide general-purpose clocking with clock multiplication and phase shifting as well as outputs for differential I/O support. Cyclone devices contain two PLLs, except for the EP1C3 device, which contains one PLL.

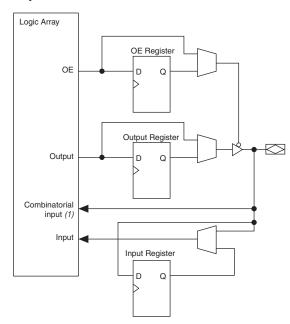


Figure 2-27. Cyclone IOE Structure

Note to Figure 2-27:

 There are two paths available for combinatorial inputs to the logic array. Each path contains a unique programmable delay chain.

The IOEs are located in I/O blocks around the periphery of the Cyclone device. There are up to three IOEs per row I/O block and up to three IOEs per column I/O block (column I/O blocks span two columns). The row I/O blocks drive row, column, or direct link interconnects. The column I/O blocks drive column interconnects. Figure 2–28 shows how a row I/O block connects to the logic array. Figure 2–29 shows how a column I/O block connects to the logic array.

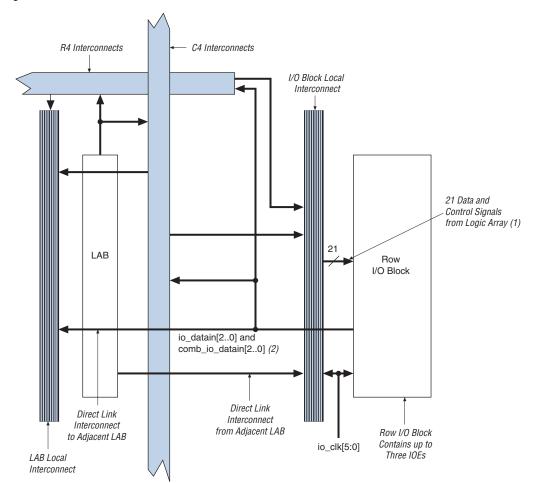


Figure 2-28. Row I/O Block Connection to the Interconnect

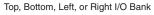
Notes to Figure 2–28:

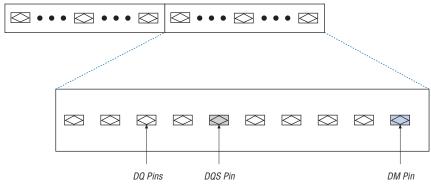
- (1) The 21 data and control signals consist of three data out lines, io_dataout[2..0], three output enables, io_coe[2..0], three input clock enables, io_cce_in[2..0], three output clock enables, io_cce_out[2..0], three clocks, io_cclk[2..0], three asynchronous clear signals, io_caclr[2..0], and three synchronous clear signals, io_csclr[2..0].
- (2) Each of the three IOEs in the row I/O block can have one io_datain input (combinatorial or registered) and one comb_io_datain (combinatorial) input.

output pins (nSTATUS and CONF_DONE) and all the JTAG pins in I/O bank 3 must operate at 2.5 V because the V_{CCIO} level of SSTL-2 is 2.5 V. I/O banks 1, 2, 3, and 4 support DQS signals with DQ bus modes of \times 8.

For ×8 mode, there are up to eight groups of programmable DQS and DQ pins, I/O banks 1, 2, 3, and 4 each have two groups in the 324-pin and 400-pin FineLine BGA packages. Each group consists of one DQS pin, a set of eight DQ pins, and one DM pin (see Figure 2–33). Each DQS pin drives the set of eight DQ pins within that group.

Figure 2–33. Cyclone Device DQ and DQS Groups in ×8 Mode Note (1)





Note to Figure 2-33:

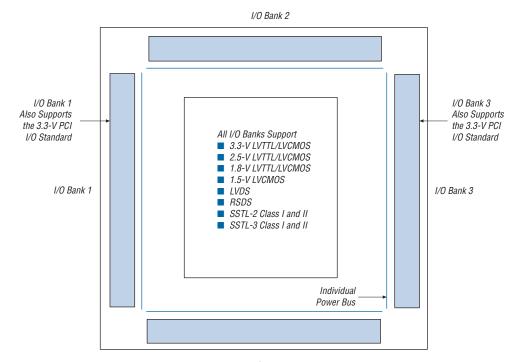
(1) Each DQ group consists of one DQS pin, eight DQ pins, and one DM pin.

Table 2–10 shows the number of DQ pin groups per device.

Table 2–10. DQ Pin Groups (Part 1 of 2)			
Device	Package	Number of × 8 DQ Pin Groups	Total DQ Pin Count
EP1C3	100-pin TQFP (1)	3	24
	144-pin TQFP	4	32
EP1C4	324-pin FineLine BGA	8	64
	400-pin FineLine BGA	8	64

and DM pins to support a DDR SDRAM or FCRAM interface. I/O bank 1 can also support a DDR SDRAM or FCRAM interface, however, the configuration input pins in I/O bank 1 must operate at 2.5 V. I/O bank 3 can also support a DDR SDRAM or FCRAM interface, however, all the JTAG pins in I/O bank 3 must operate at 2.5 V.

Figure 2–35. Cyclone I/O Banks Notes (1), (2)



I/O Bank 4

Notes to Figure 2–35:

- (1) Figure 2–35 is a top view of the silicon die.
- (2) Figure 2–35 is a graphic representation only. Refer to the pin list and the Quartus II software for exact pin locations.

Each I/O bank has its own VCCIO pins. A single device can support 1.5-V, 1.8-V, 2.5-V, and 3.3-V interfaces; each individual bank can support a different standard with different I/O voltages. Each bank also has dual-purpose VREF pins to support any one of the voltage-referenced standards (e.g., SSTL-3) independently. If an I/O bank does not use voltage-referenced standards, the $V_{\rm REF}$ pins are available as user I/O pins.

The Cyclone device instruction register length is 10 bits and the USERCODE register length is 32 bits. Tables 3–2 and 3–3 show the boundary-scan register length and device IDCODE information for Cyclone devices.

Table 3–2. Cyclone Boundary-Scan Register Length		
Device	Boundary-Scan Register Length	
EP1C3	339	
EP1C4	930	
EP1C6	582	
EP1C12	774	
EP1C20	930	

Table 3–3	Table 3–3. 32-Bit Cyclone Device IDCODE					
	IDCODE (32 bits) (1)					
Device	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	LSB (1 Bit) (2)		
EP1C3	0000	0010 0000 1000 0001	000 0110 1110	1		
EP1C4	0000	0010 0000 1000 0101	000 0110 1110	1		
EP1C6	0000	0010 0000 1000 0010	000 0110 1110	1		
EP1C12	0000	0010 0000 1000 0011	000 0110 1110	1		
EP1C20	0000	0010 0000 1000 0100	000 0110 1110	1		

Notes to Table 3-3:

- (1) The most significant bit (MSB) is on the left.
- (2) The IDCODE's least significant bit (LSB) is always 1.

Table 4–16. Cyclone Device Capacitance Note (14)			
Symbol	Parameter	Typical	Unit
C _{IO}	Input capacitance for user I/O pin	4.0	pF
C _{LVDS}	Input capacitance for dual-purpose LVDS/user I/O pin	4.7	pF
C _{VREF}	Input capacitance for dual-purpose V _{REF} /user I/O pin.	12.0	pF
C _{DPCLK}	Input capacitance for dual-purpose DPCLK/user I/O pin.	4.4	pF
C _{CLK}	Input capacitance for CLK pin.	4.7	pF

Notes to Tables 4–1 through 4–16:

- (1) Refer to the Operating Requirements for Altera Devices Data Sheet.
- (2) Conditions beyond those listed in Table 4–1 may cause permanent damage to a device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse affects on the device.
- (3) Minimum DC input is -0.5 V. During transitions, the inputs may undershoot to -2.0 V or overshoot to 4.6 V for input currents less than 100 mA and periods shorter than 20 ns.
- (4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
- (5) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (6) Typical values are for $T_A = 25^{\circ}$ C, $V_{CCINT} = 1.5$ V, and $V_{CCIO} = 1.5$ V, 1.8 V, 2.5 V, and 3.3 V.
- (7) V_I = ground, no load, no toggling inputs.
- (8) This value is specified for normal device operation. The value may vary during power-up. This applies for all V_{CCIO} settings (3.3, 2.5, 1.8, and 1.5 V).
- (9) R_{CONF} is the measured value of internal pull-up resistance when the I/O pin is tied directly to GND. R_{CONF} value will be lower if an external source drives the pin higher than V_{CCIO}.
- (10) Pin pull-up resistance values will lower if an external source drives the pin higher than V_{CCIO}.
- (11) Drive strength is programmable according to values in Cyclone Architecture chapter in the Cyclone Device Handbook.
- (12) Overdrive is possible when a 1.5 V or 1.8 V and a 2.5 V or 3.3 V input signal feeds an input pin. Turn on "Allow voltage overdrive" for LVTTL/LVCMOS input pins in the Assignments > Device > Device and Pin Options > Pin Placement tab when a device has this I/O combination. However, higher leakage current is expected.
- (13) The Cyclone LVDS interface requires a resistor network outside of the transmitter channels.
- (14) Capacitance is sample-tested only. Capacitance is measured using time-domain reflections (TDR). Measurement accuracy is within ±0.5 pF.

Power Consumption

Designers can use the Altera web Early Power Estimator to estimate the device power.

Cyclone devices require a certain amount of power-up current to successfully power up because of the nature of the leading-edge process on which they are fabricated. Table 4–17 shows the maximum power-up current required to power up a Cyclone device.

Table 4–17. Cyclone Maximum Power-Up Current (I _{CCINT}) Requirements (In-Rush Current)			
Device	Commercial Specification	Industrial Specification	Unit
EP1C3	150	180	mA
EP1C4	150	180	mA
EP1C6	175	210	mA
EP1C12	300	360	mA
EP1C20	500	600	mA

Notes to Table 4–17:

- The Cyclone devices (except for the EP1C20 device) meet the power up specification for Mini PCI.
- (2) The lot codes 9G0082 to 9G2999, or 9G3109 and later comply to the specifications in Table 4–17 and meet the Mini PCI specification. Lot codes appear at the top of the device.
- (3) The lot codes 9H0004 to 9H29999, or 9H3014 and later comply to the specifications in this table and meet the Mini PCI specification. Lot codes appear at the top of the device.

Designers should select power supplies and regulators that can supply this amount of current when designing with Cyclone devices. This specification is for commercial operating conditions. Measurements were performed with an isolated Cyclone device on the board. Decoupling capacitors were not used in this measurement. To factor in the current for decoupling capacitors, sum up the current for each capacitor using the following equation:

$$I = C (dV/dt)$$

The exact amount of current that is consumed varies according to the process, temperature, and power ramp rate. If the power supply or regulator can supply more current than required, the Cyclone device may consume more current than the maximum current specified in Table 4–17. However, the device does not require any more current to successfully power up than what is listed in Table 4–17.

The duration of the I_{CCINT} power-up requirement depends on the V_{CCINT} voltage supply rise time. The power-up current consumption drops when the V_{CCINT} supply reaches approximately 0.75 V. For example, if the V_{CCINT} rise time has a linear rise of 15 ms, the current consumption spike drops by 7.5 ms.

			Resources Used			Performance		
Resource Used	Design Size and Function	Mode	LEs	M4K Memory Bits	M4K Memory Blocks	-6 Speed Grade (MHz)	-7 Speed Grade (MHz)	-8 Speed Grade (MHz)
M4K	RAM 128 × 36 bit	Single port	_	4,608	1	256.00	222.67	197.01
memory block	RAM 128 × 36 bit	Simple dual-port mode	_	4,608	1	255.95	222.67	196.97
	RAM 256 × 18 bit	True dual- port mode	_	4,608	1	255.95	222.67	196.97
	FIFO 128 × 36 bit	_	40	4,608	1	256.02	222.67	197.01
	Shift register 9 × 4 × 128	Shift register	11	4,536	1	255.95	222.67	196.97

Note to Table 4-20:

Internal Timing Parameters

Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–21 through 4–24 describe the Cyclone device internal timing microparameters for LEs, IOEs, M4K memory structures, and MultiTrack interconnects.

Table 4–21. LE Internal Timing Microparameter Descriptions		
Symbol	Parameter	
t _{SU}	LE register setup time before clock	
t _H	LE register hold time after clock	
t _{CO}	LE register clock-to-output delay	
t _{LUT}	LE combinatorial LUT delay for data-in to data-out	
t _{CLR}	Minimum clear pulse width	
t _{PRE}	Minimum preset pulse width	
t _{CLKHL}	Minimum clock high or low time	

⁽¹⁾ The performance numbers for this function are from an EP1C6 device in a 240-pin PQFP package.

Referenced Document

This chapter references the following documents:

- Cyclone Architecture chapter in the Cyclone Device Handbook
- Operating Requirements for Altera Devices Data Sheet

Document Revision History

Table 4–53 shows the revision history for this chapter.

Table 4-53. Do	Table 4–53. Document Revision History			
Date and Document Version	Changes Made	Summary of Changes		
May 2008 v1.7	Minor textual and style changes. Added "Referenced Document" section.	_		
January 2007 v1.6	 Added document revision history. Added new row for V_{CCA} details in Table 4–1. Updated R_{CONF} information in Table 4–3. Added new <i>Note</i> (12) on voltage overdrive information to Table 4–7 and Table 4–8. Updated <i>Note</i> (9) on R_{CONF} information to Table 4–3. Updated information in "External I/O Delay Parameters" section. Updated speed grade information in Table 4–46 and Table 4–47. Updated LVDS information in Table 4–51. 	_		
August 2005 v1.5	Minor updates.	_		
February 2005 v1.4	 Updated information on Undershoot voltage. Updated Table 4-2. Updated Table 4-3. Updated the undershoot voltage from 0.5 V to 2.0 V in Note 3 of Table 4-16. Updated Table 4-17. 	_		
January 2004 v.1.3	 Added extended-temperature grade device information. Updated Table 4-2. Updated I_{CC0} information in Table 4-3. 	_		
October 2003 v.1.2	 Added clock tree information in Table 4-19. Finalized timing information for EP1C3 and EP1C12 devices. Updated timing information in Tables 4-25 through 4-26 and Tables 4-30 through 4-51. Updated PLL specifications in Table 4-52. 	_		

July 2003 v1.1	Updated timing information. Timing finalized for EP1C6 and EP1C20 devices. Updated performance information. Added PLL Timing section.	_
May 2003 v1.0	Added document to Cyclone Device Handbook.	_



5. Reference and Ordering Information

C51005-1.4

Software

Cyclone® devices are supported by the Altera® Quartus® II design software, which provides a comprehensive environment for system-on-a-programmable-chip (SOPC) design. The Quartus II software includes HDL and schematic design entry, compilation and logic synthesis, full simulation and advanced timing analysis, SignalTap® II logic analysis, and device configuration.



For more information about the Quartus II software features, refer to the *Quartus II Handbook*.

The Quartus II software supports the Windows 2000/NT/98, Sun Solaris, Linux Red Hat v7.1 and HP-UX operating systems. It also supports seamless integration with industry-leading EDA tools through the NativeLink® interface.

Device Pin-Outs

Device pin-outs for Cyclone devices are available on the Altera website (www.altera.com) and in the *Cyclone Device Handbook*.

Ordering Information

Figure 5–1 describes the ordering codes for Cyclone devices. For more information about a specific package, refer to the *Package Information for Cyclone Devices* chapter in the *Cyclone Device Handbook*.

February 2005 v1.1	Updated Figure 5-1.	_
May 2003 v1.0	Added document to Cyclone Device Handbook.	_